

Study of the IBF of Double/Triple THGEM

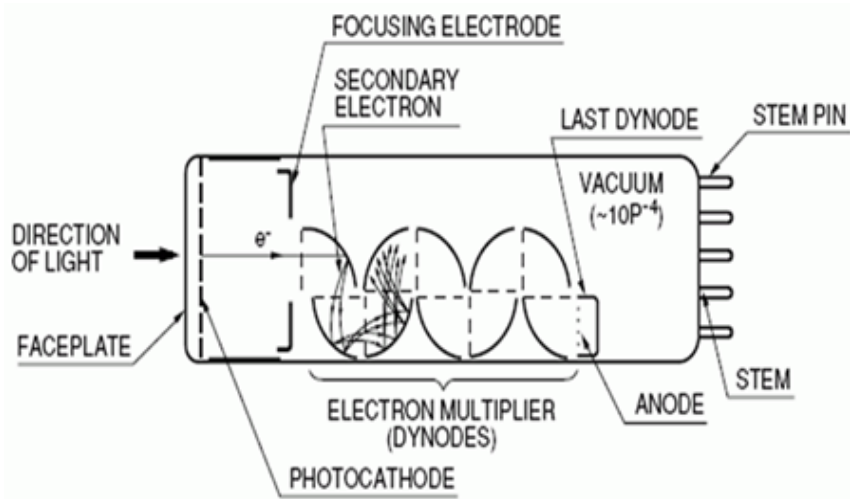
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NED 2012, Mianyang

Outline

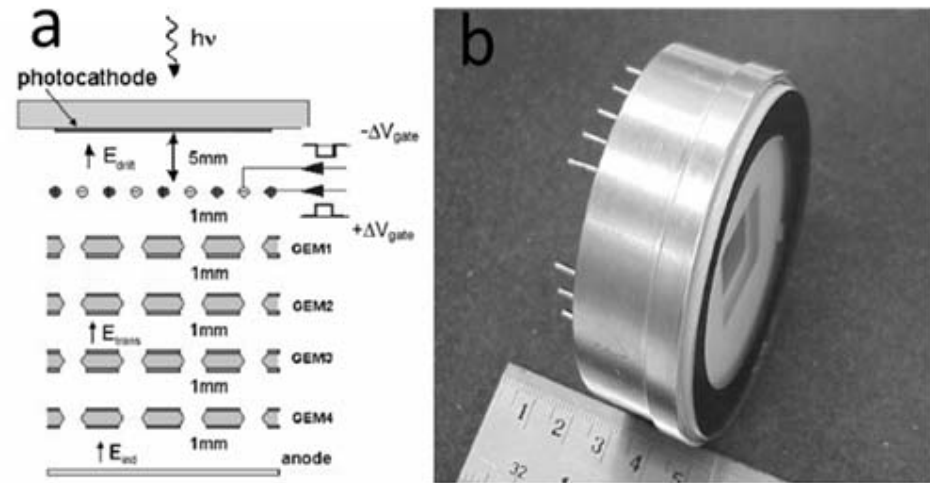
- PMT/Gas PMT
- THGEM introduction
- IBF of DTHGEM study
- Triple THGEM study
- Combined analysis
- Conclusion

Photo Multiplier Tube (PMT)



PMT

1. High Gain
2. Excellent time resolution (ps)
3. Output channel limited
4. Magnetic field deflected
5. Expensive

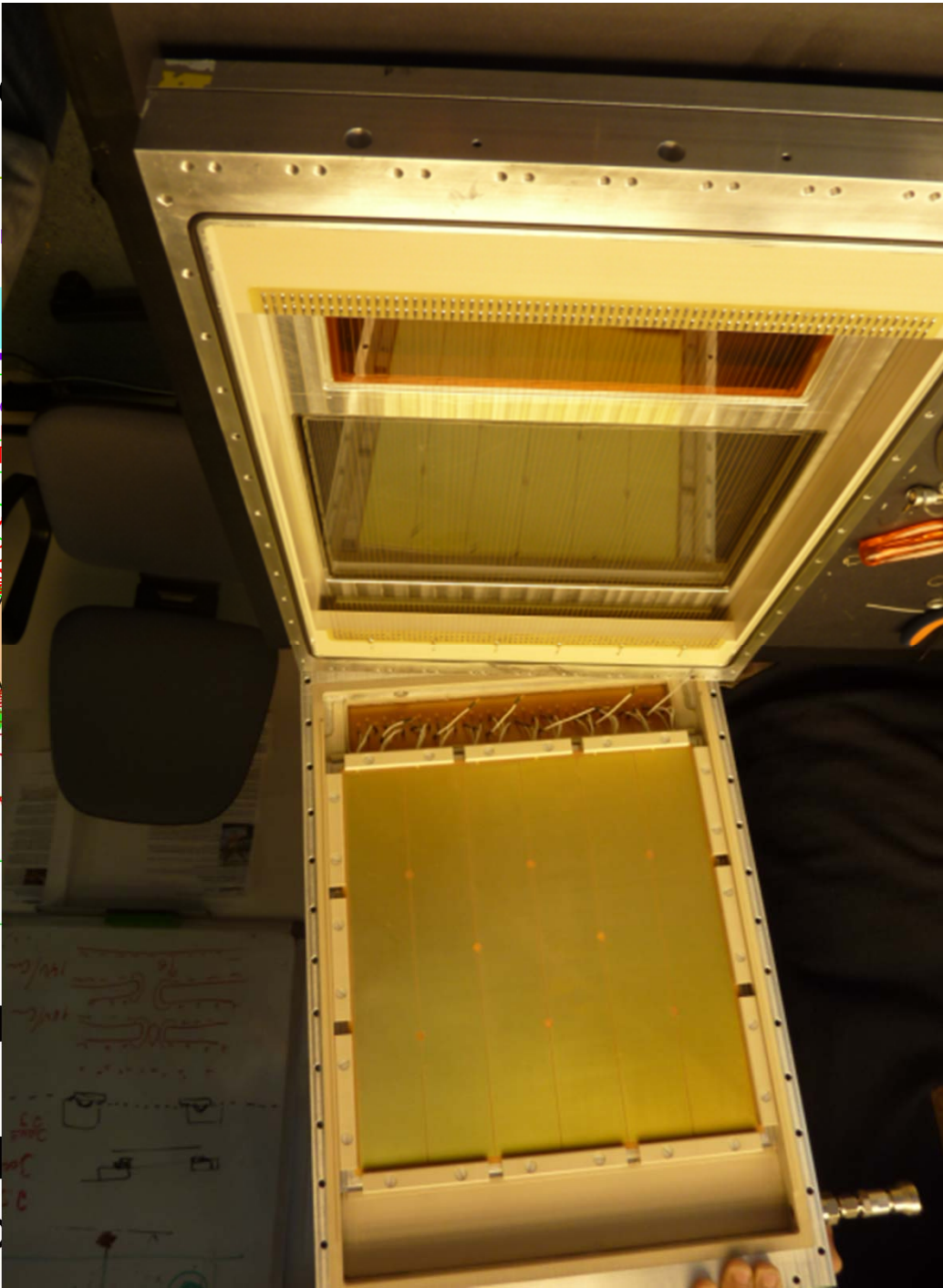
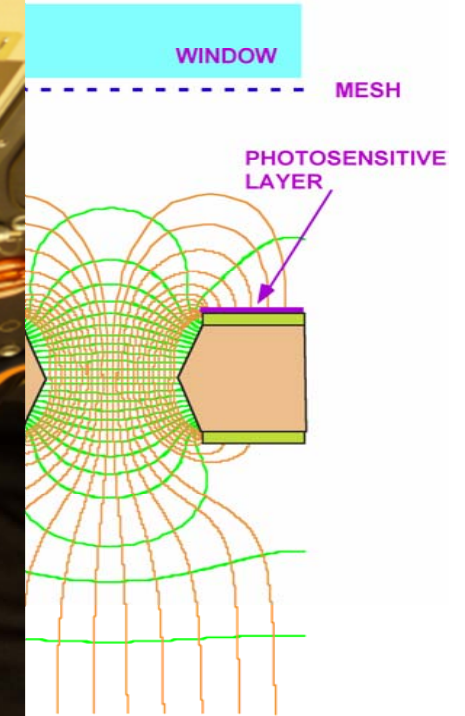
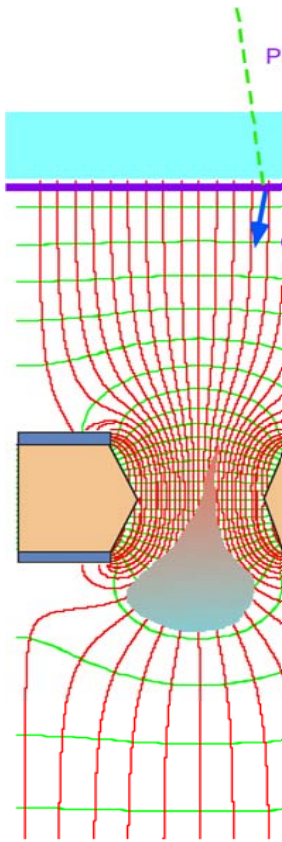


Gas PMT

1. High Gain
2. Good time resolution (ns)
3. Multi-Channel output
4. Magnetic field tolerated
5. Radiation hard
6. Relatively cheap
7. Compact

Principle

Coating



Transfer

Effect

In both methods, the spray material hits on photoresist.

Electric field and

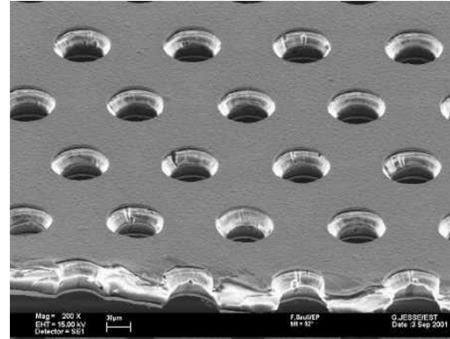
Thicker Gas Electron Multiplier (THGEM)

Standard GEM

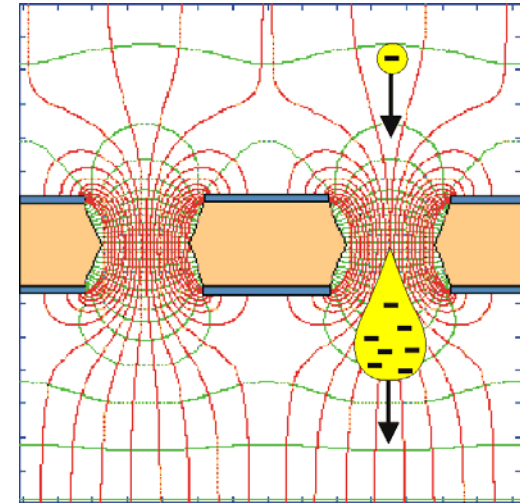
Developed from 1997 by F. Sauli (CERN)

Typical parameters:

- $50\mu\text{m}$ Kapton
- $\text{Ø}60\mu\text{m}$ holes
- $100\text{-}200\mu\text{m}$ pitch



F. Sauli NIM A 433 (1997) 531



THGEM

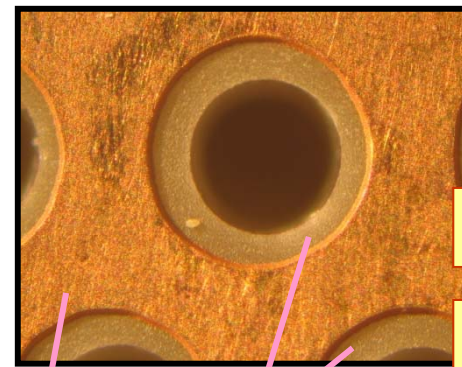
Developed from 2004 by A. Breskin (Israel, CERN) :

Parameters:

Thickness $t = 0.2\sim 0.5\text{ mm}$

Hole diameter $d = 0.2 - 1\text{ mm}$

Pitch $a = 0.5 - 1\text{ mm}$



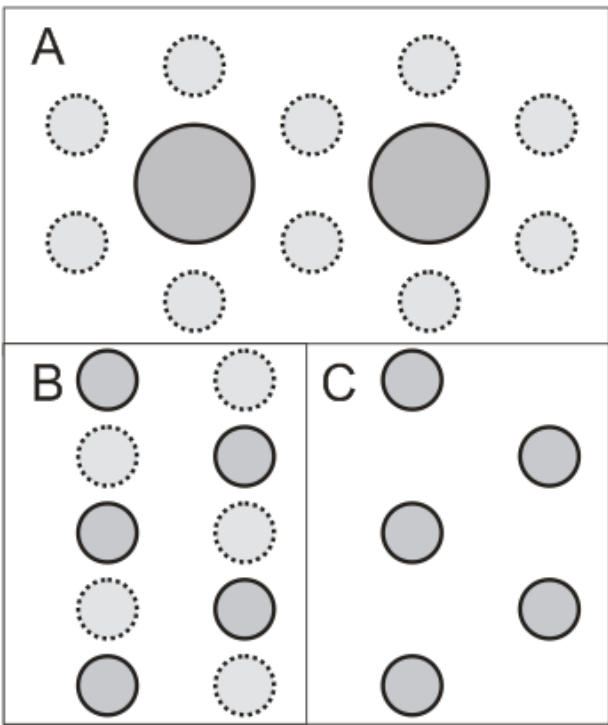
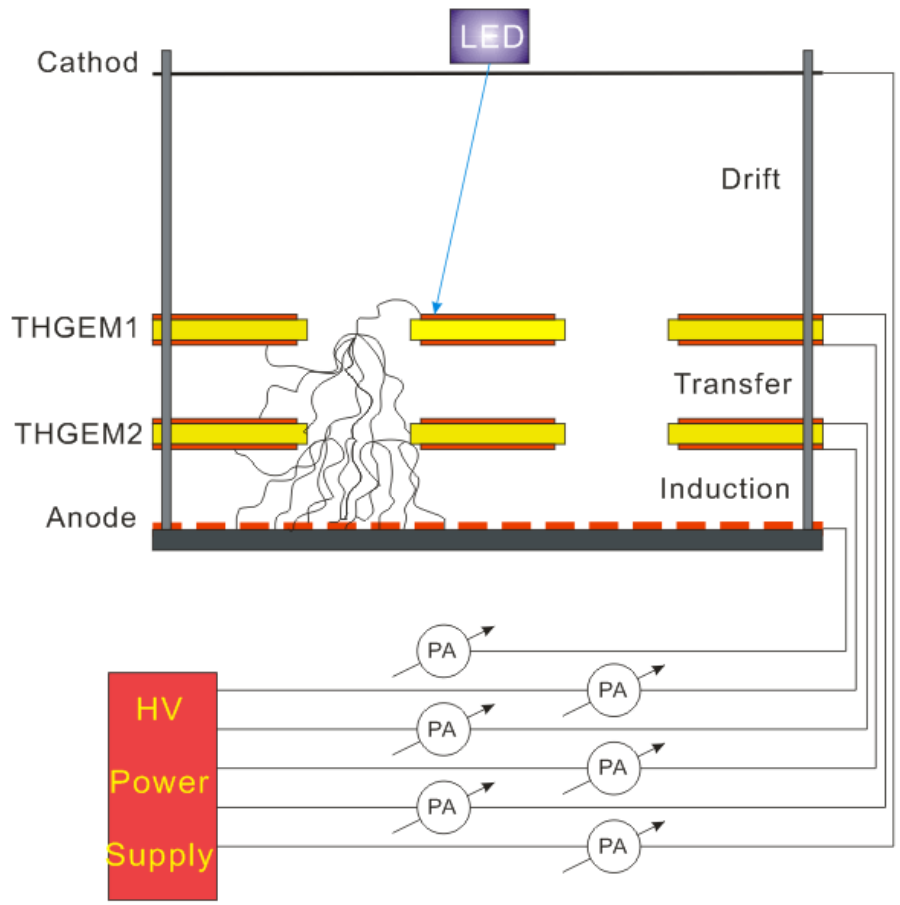
Cu G-10

ROBUST !

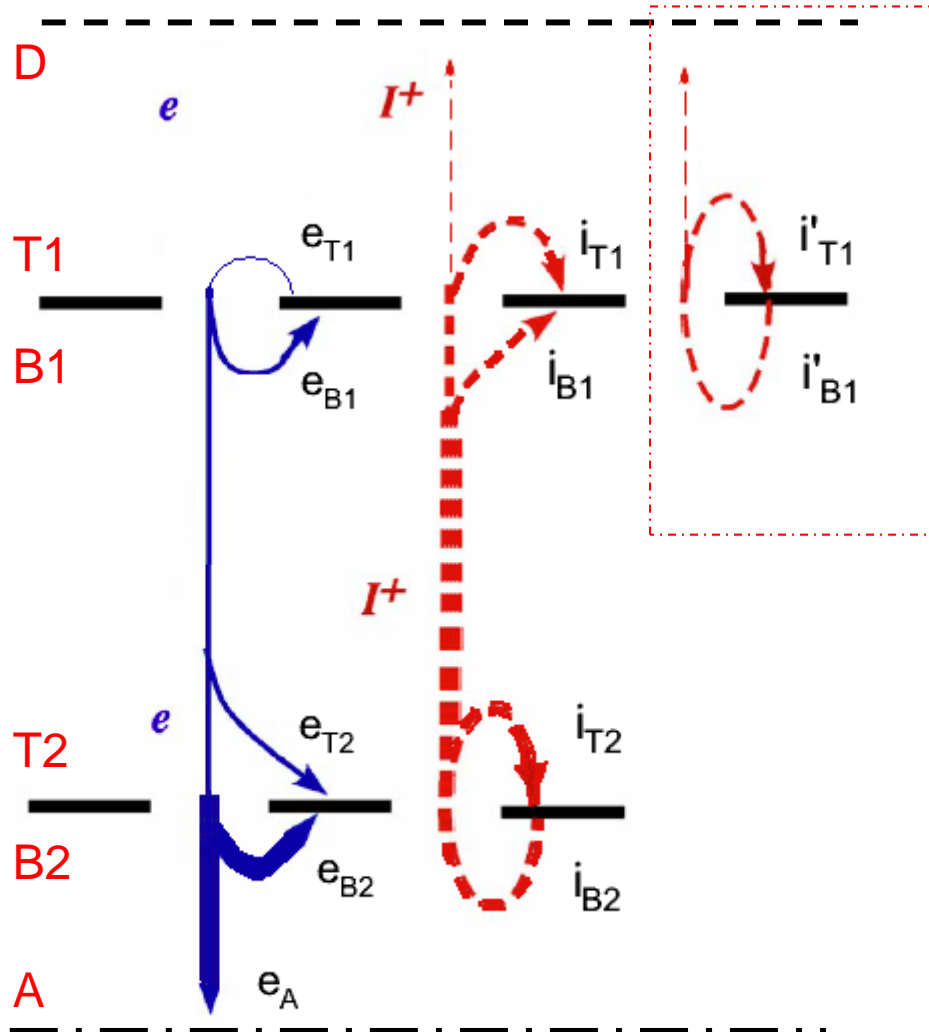
Easy produced

Chechik et al. NIM A535 (2004) 303

Experiment setup



Different pattern designs of THGEM



$$e_{B1}, e_{T2}, i'_{T1} \propto \text{Gain}$$

$$e_{B2}, e_A, i_{T1}, i_{B1}, i_{T2}, i_{B2} \propto \text{Gain}^2$$

Almost 0

negligible

$$I_{T1} = i_{T1} + i'_{T1} - e_{T1}$$

$$I_{B1} = i_{B1} - e_{B1} + i'_{B1}$$

$$I_{T2} = i_{T2} - e_{T2}$$

$$I_{B2} = -e_{B2} + i_{B2}$$

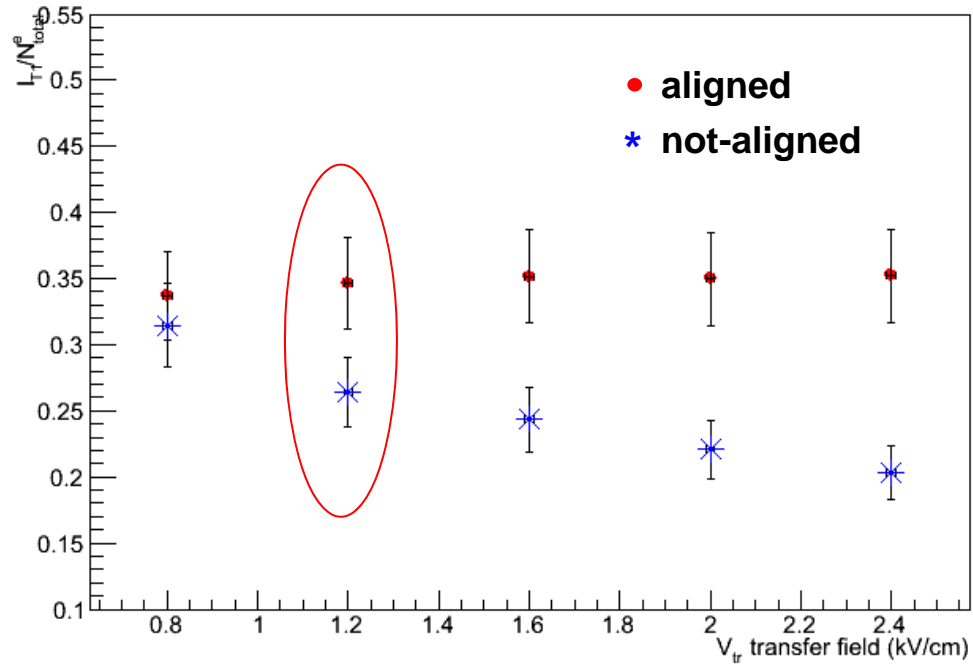
$$I_A = -e_A$$

$$I_{total}^e = |e_A + e_{B2} + e_{T2} + e_{B1}|$$

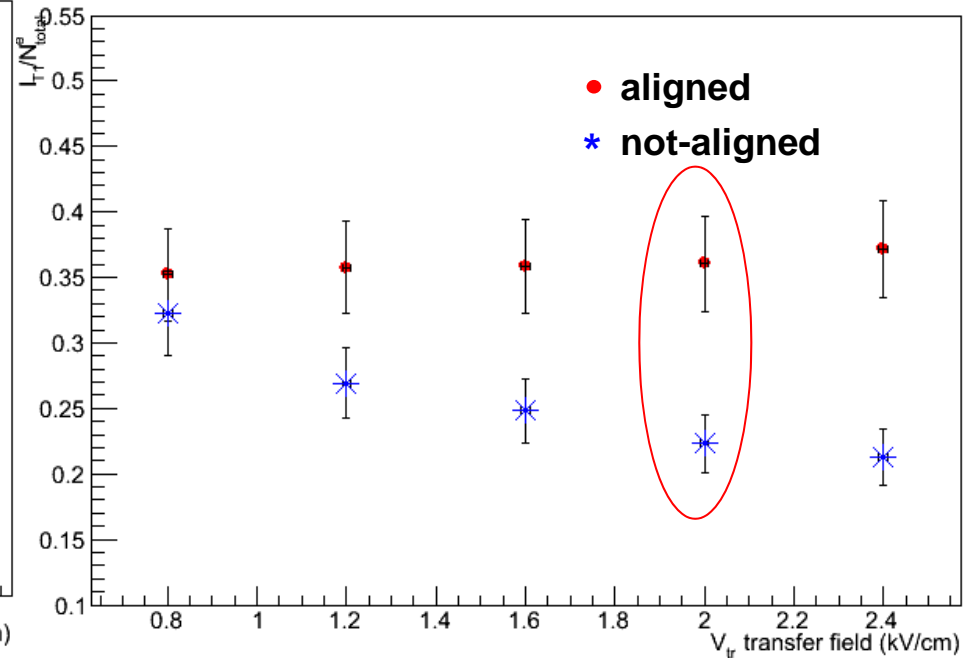
$$\rightarrow |I_A + I_{B2}| = |e_A + e_{B2} - i_{B2}|$$

IBF measurement (T_1/T_{Tot}) for Conf. B/C

The IBF for 1.2kV/cm induction field



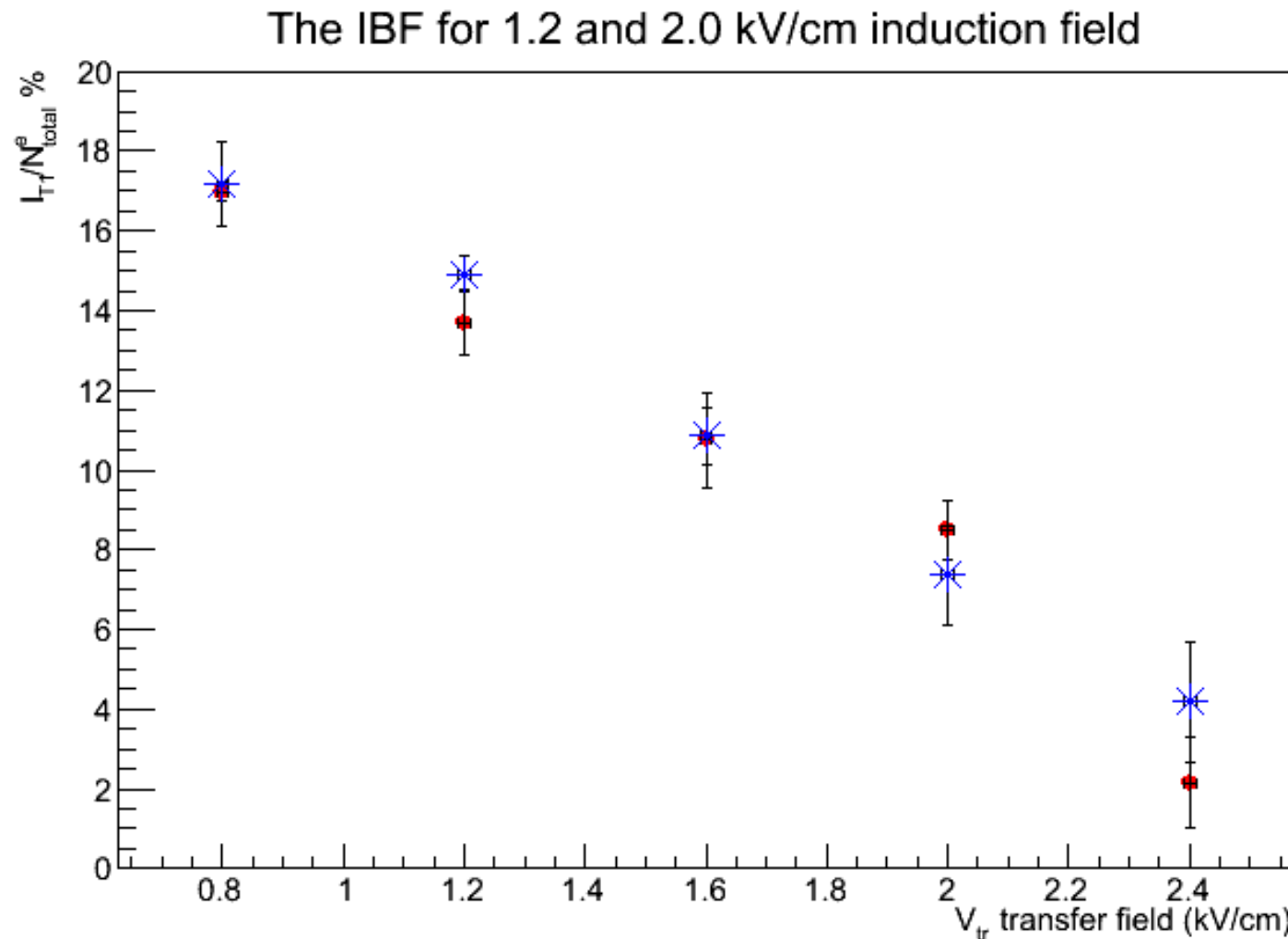
The IBF for 2.0kV/cm induction field



For aligned DTHGEM, the IBF is not related to the transfer field.

For not-aligned DTHGEM, the IBF decreases while transfer field increases.

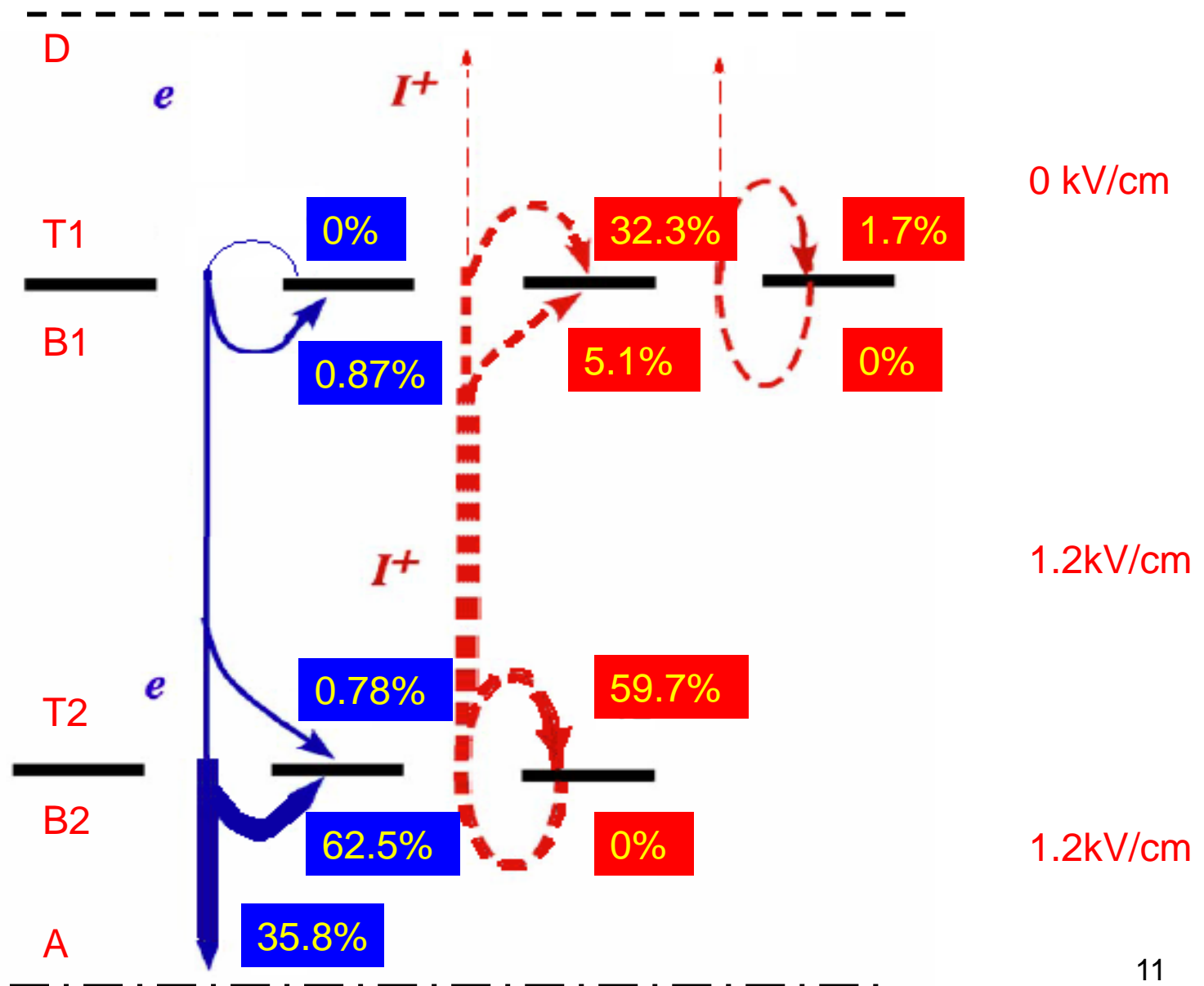
IBF measurement for conf. A(T1/Tot)



The IBF decreases dramatically while transfer field increases.

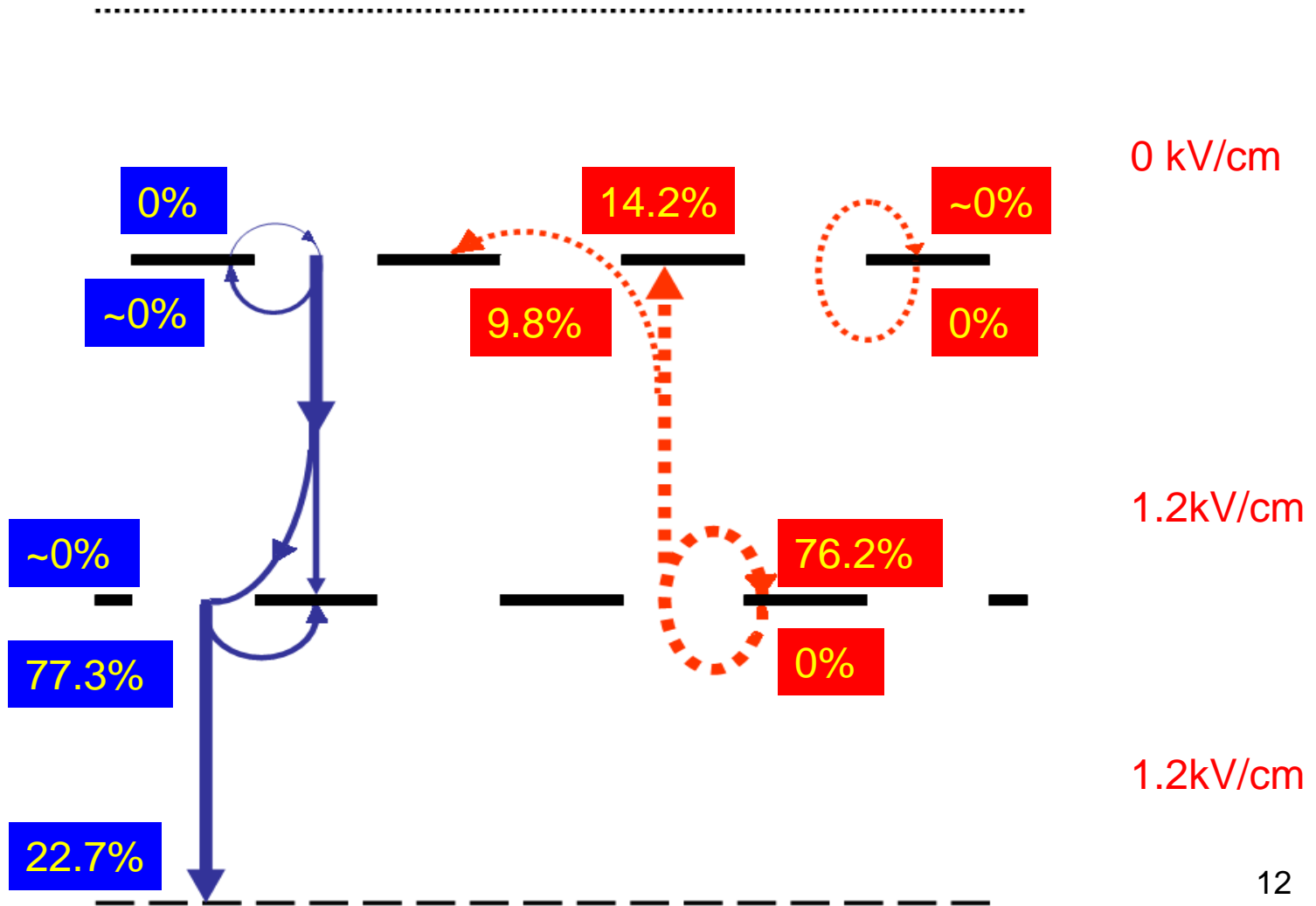
Errors are calculated using the error propagation function.

IBF analysis for conf. C (aligned)



IBF analysis for conf. A

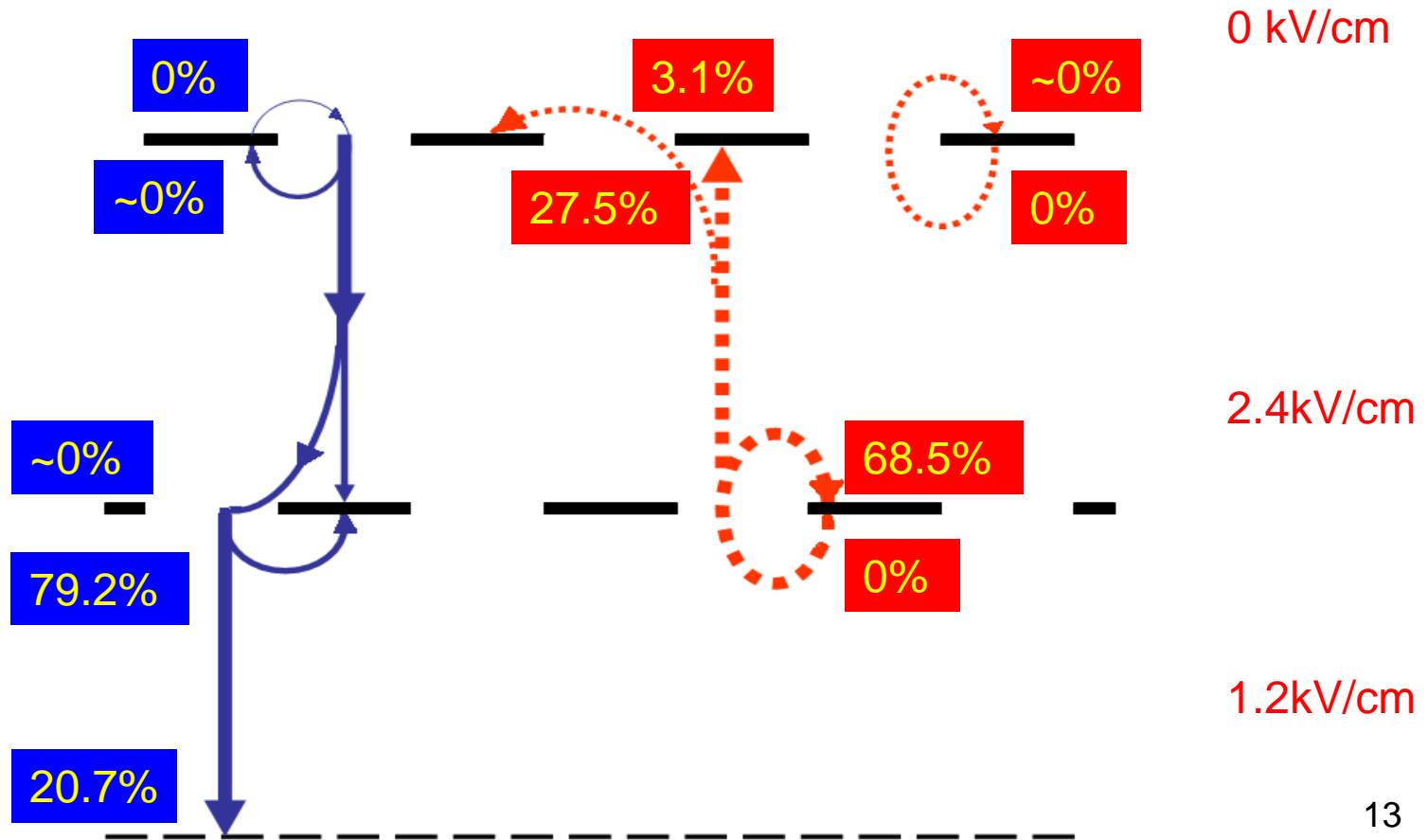
Gain was pushed to the second THGEM,
so the electrons and ions from the first layer of THGEM are almost negligible.



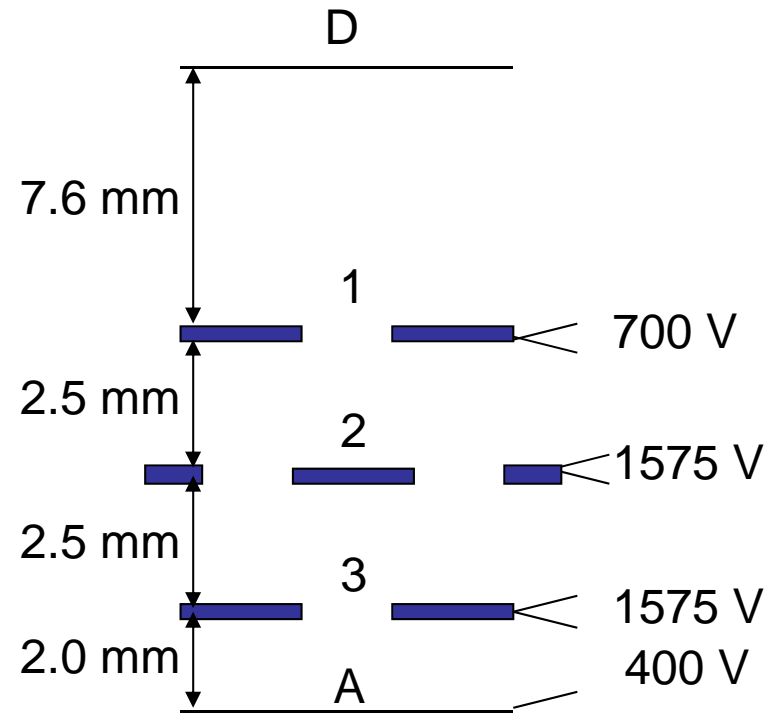
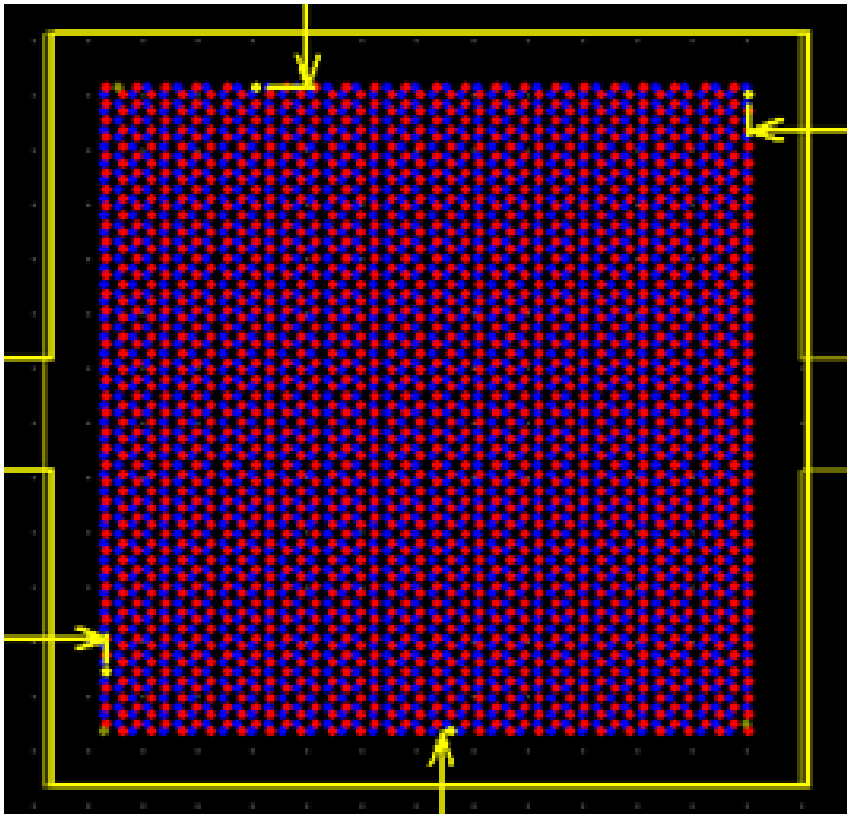
IBF analysis for conf. A

Double the transfer field, the ions will hit B1 instead of drifting to T1.

But the ions from bottom are still mainly collected by T2.



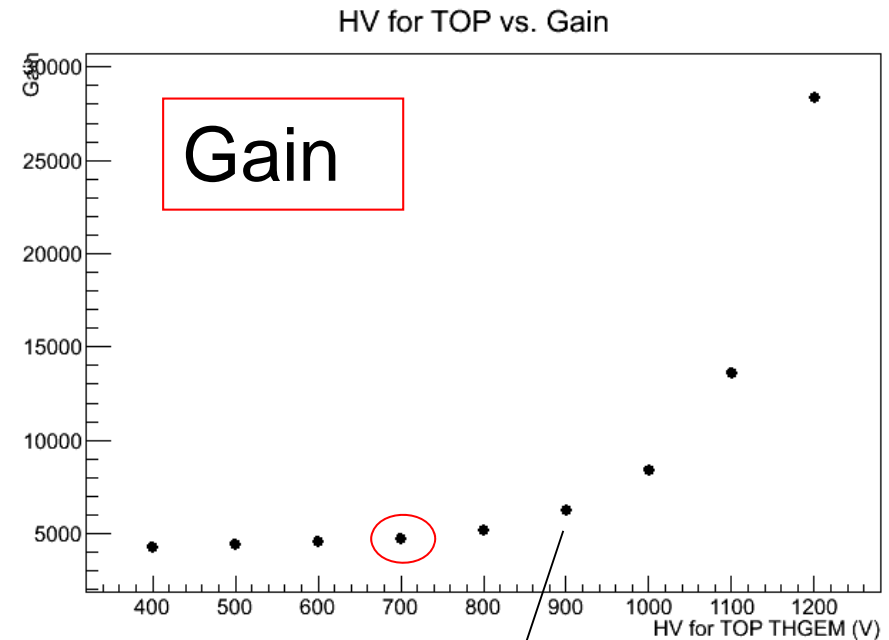
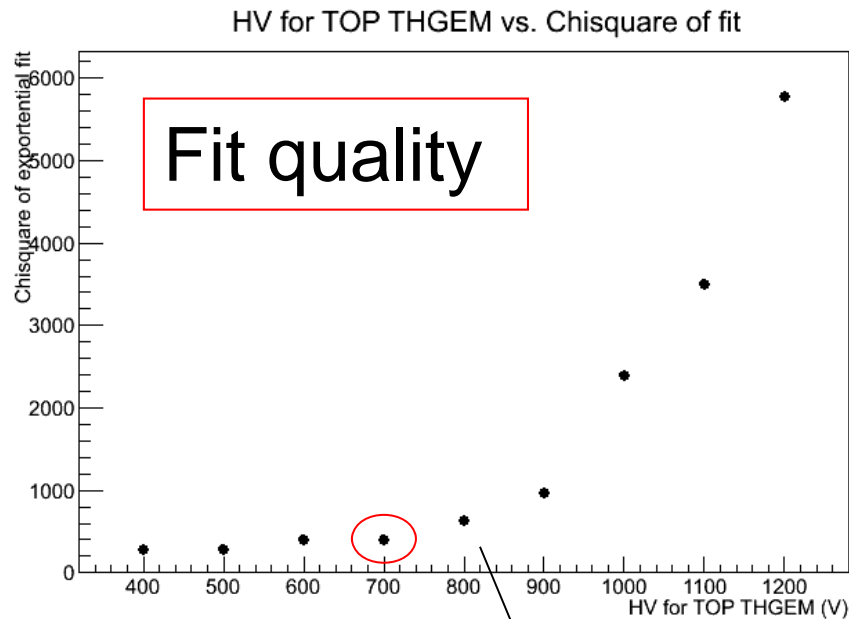
Triple THGEM configuration



Conf. B is used for triple THGEM. The middle one is not aligned to the others two.

Scan the top THGEM HV

To push the gain to the bottom two, TOP THGEM high voltage is set to **700V**.

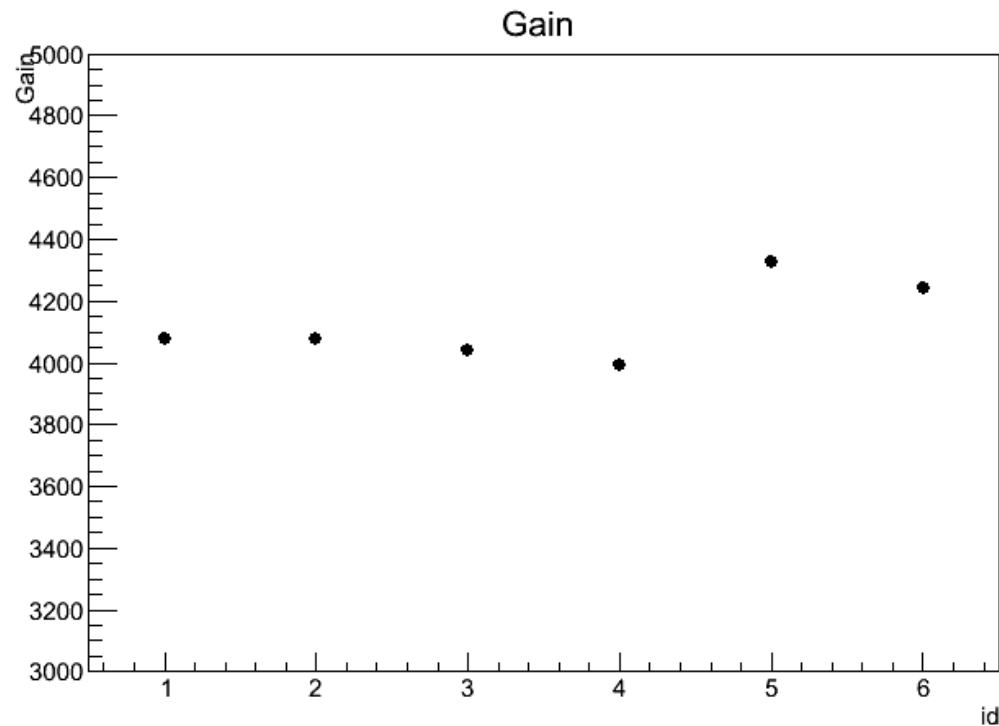


- The quality of the fit starts to get worse at 800V/0.4cm.
- The gain shows lower than 900V/0.4cm, the single photon is dominated.
Starting at 900V/0.4cm, the multiple photons are dominated, and the top THGEM starts to work.

UV light stability

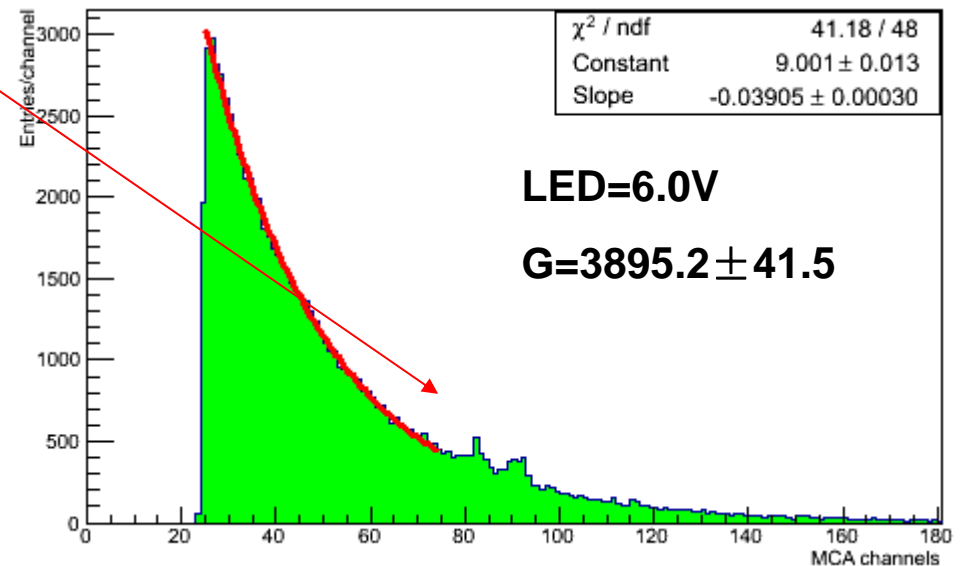
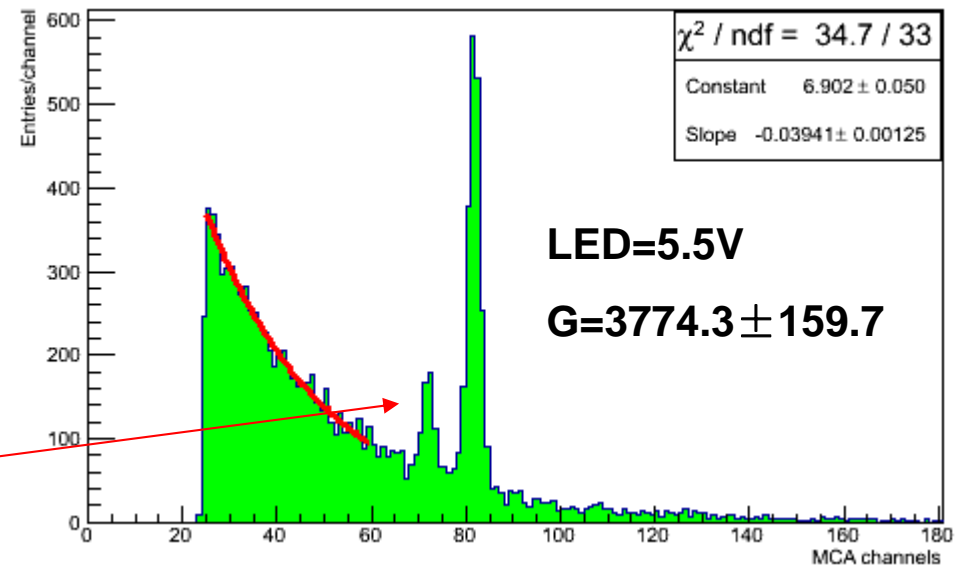
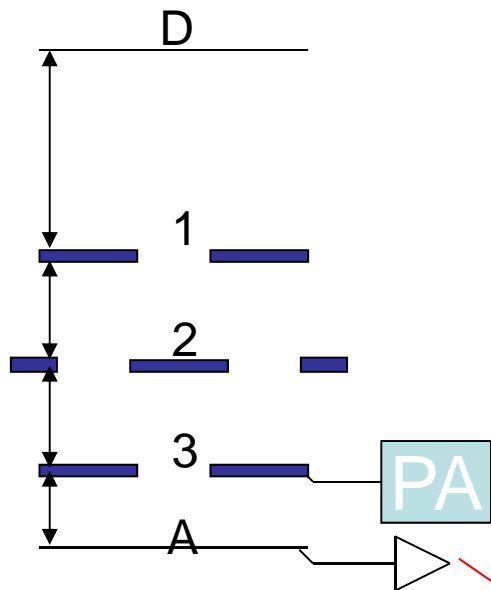
Motivation: during DTHGEM test, the current of anode decreased when induction field increased. One probability is the UV light intensity decreased.

Method: Applying 6.5 V to UV light, turn it on for 1 min which is approximately the same time period for IBF measurement, then turn it off for another 1 or 2 minutes.



The light source should be quite stable during the IBF measurement!

UV light vs. PA Meter



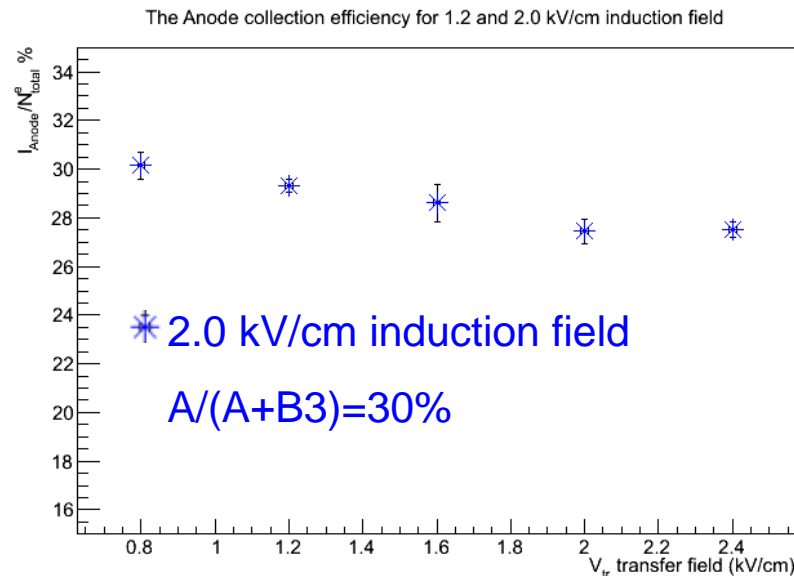
The noise from PA contribution can be avoid by chose a different fit range.

UV light vs. PA Meter

The anode current can be estimate by:

$$I_{\text{Anode}} = e \times \text{Gain} \times \text{Rate} / e^{-\text{Thres}/(e \times \text{Gain})}$$

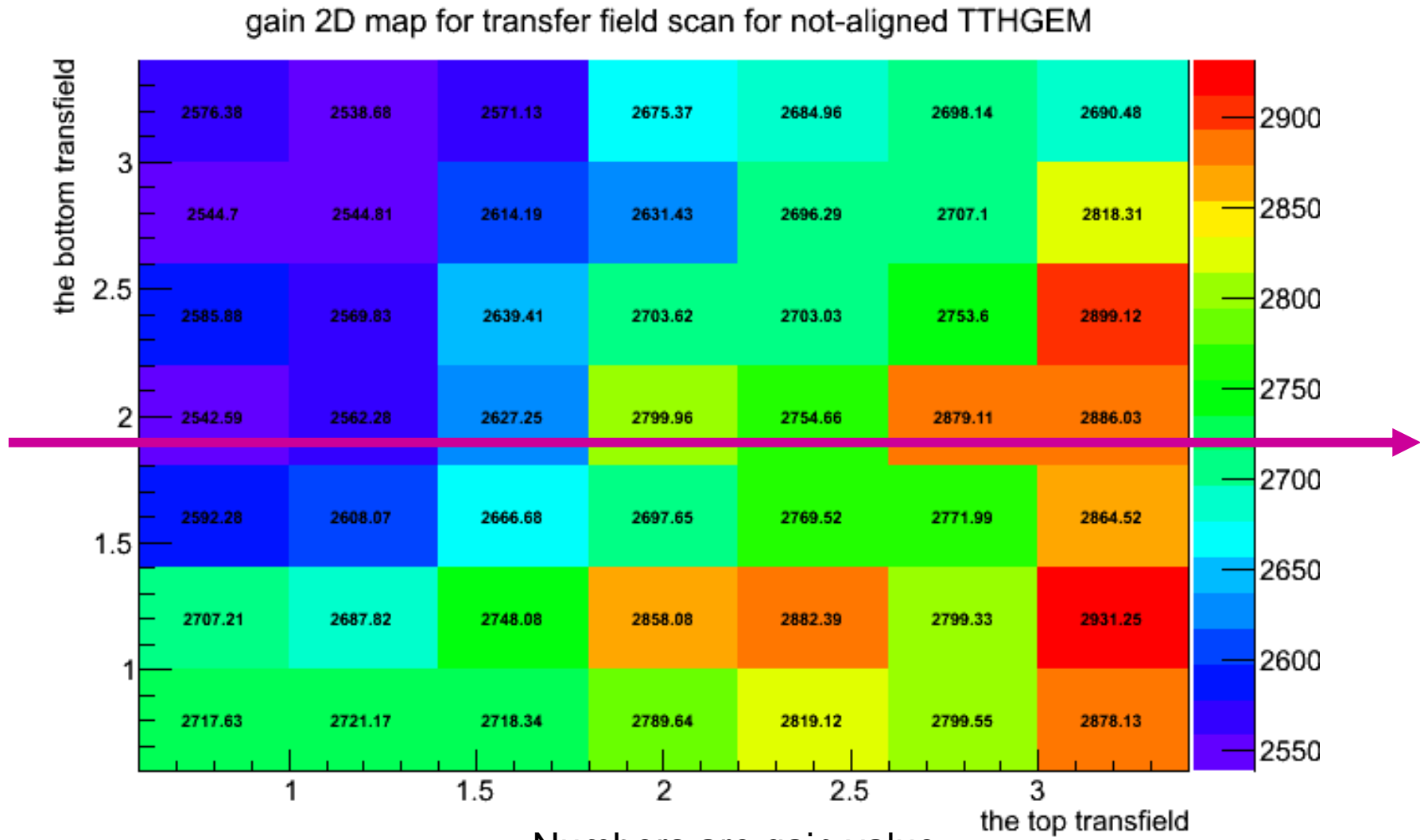
LED	Thres./fC	Rate/Hz	Gain	I_Anode	I_Anode'	I_B3
5.5	1.12	550	3774.3	-2.12	-3.0	-7
6.0	1.12	6975	3895.2	-26.22	-37.7	-88
6.5	1.12	27947	4172.2	-99.87	-165	-385



Measured from PA Meter

Gain 2D scan for not-aligned TTHGEM

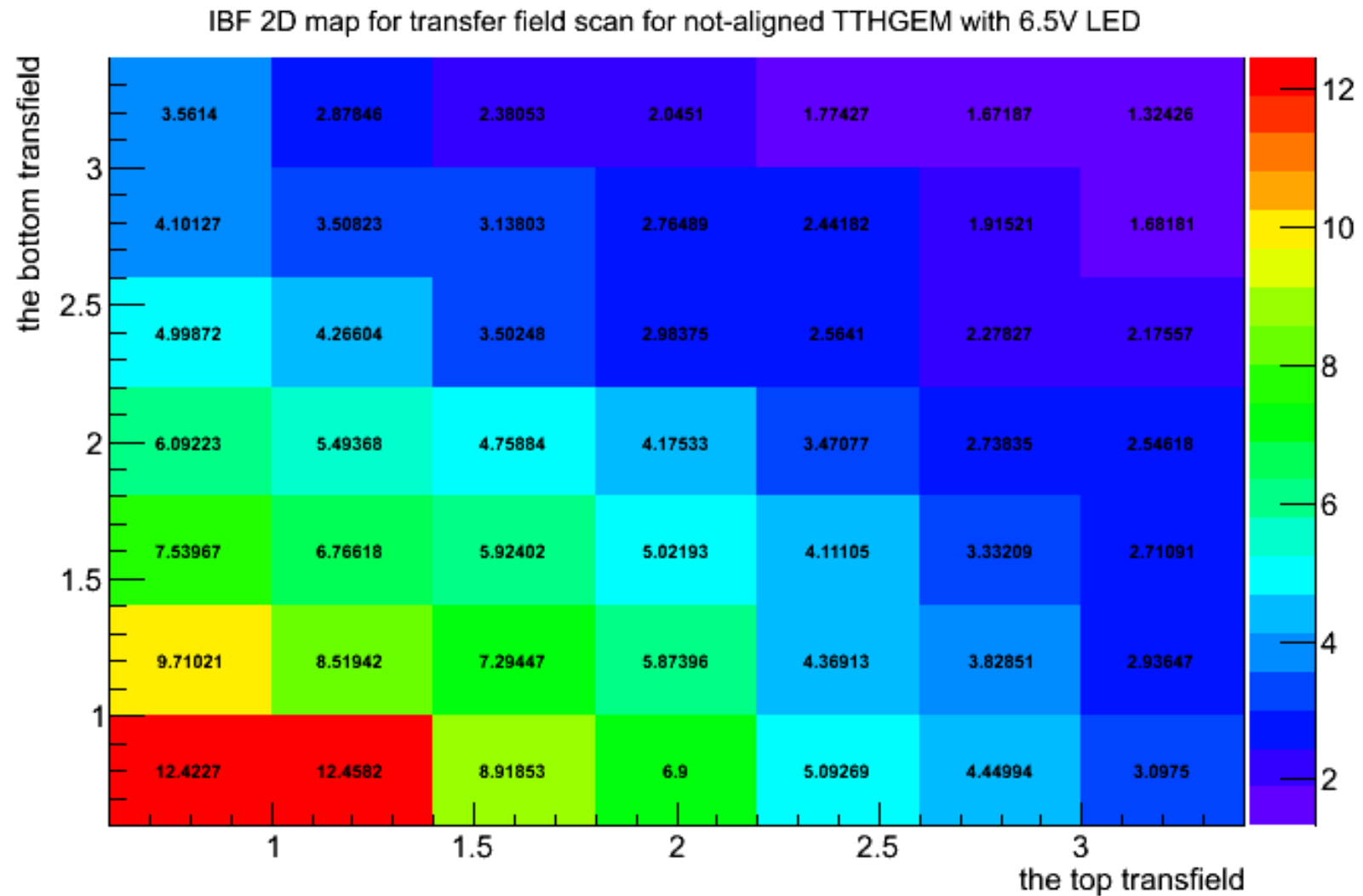
Gain doesn't change much. But with larger bottom transfer field, the gain is smaller.



Numbers are gain value.

The test has been done with LED=5.5V

IBF 2D scan for not-aligned TTHGEM



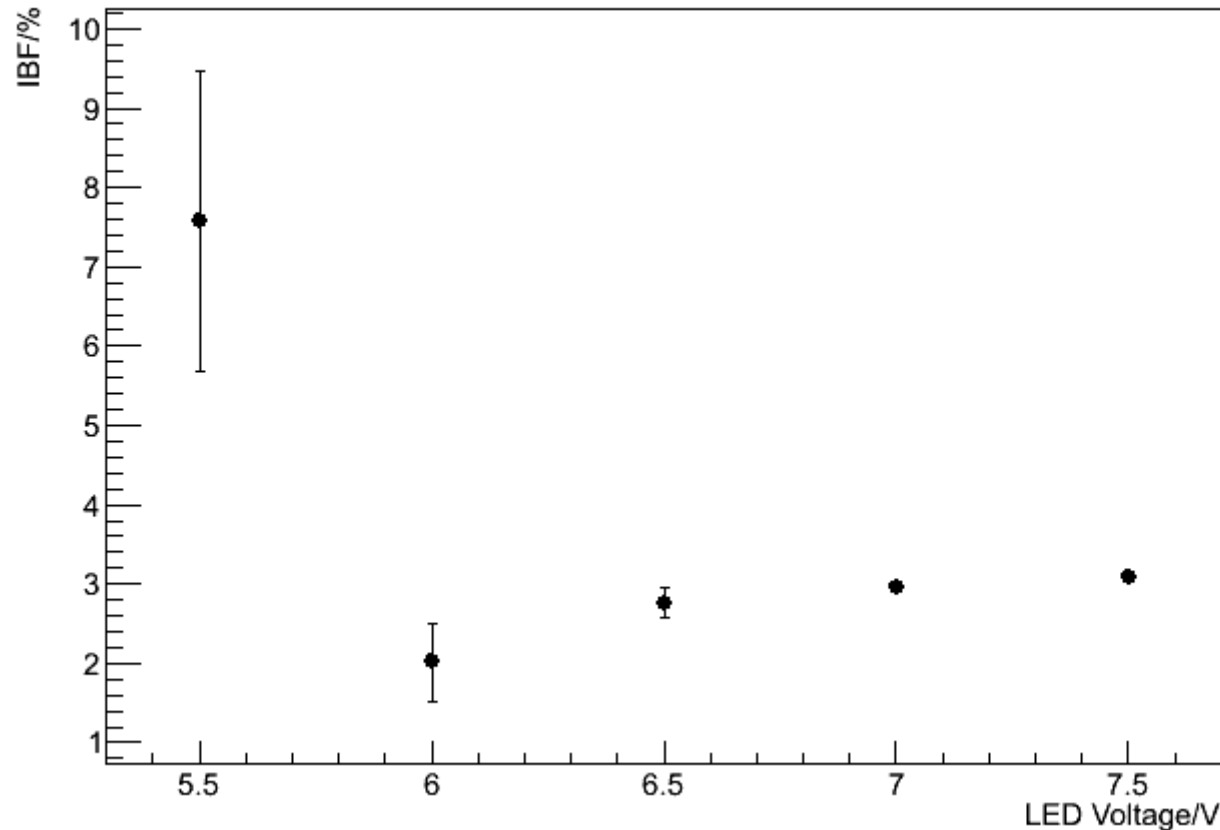
Numbers are IBF%

IBF vs. LED for not-aligned TTHGEM

The top transfer field = 3.0kV/cm

The bottom transfer field = 2.0kV/cm

IBF vs. LED voltage



The error are calculated by error propagation.

By increasing LED voltage, the uncertainty of IBF decreases because the current is bigger and more stable

The IBF 2D scan result for 5.5V LED can be found in the backup slices.

discussion

- The not-aligned conf. can decrease 93.3% IBF, while only lose 17% gain.
- Question followed:
 1. will this not-aligned conf. decrease the max counting rate?
 2. will this not-aligned conf. decrease the efficiency?
- Due to the PA meter, IBF is measured for LED=6.5 V;
- To have “single” photon-electron signals, gain is measured for LED=5.5V

$$I_{\text{Anode}} = \underline{e \times \text{Gain} \times \text{Rate}} / e^{-\text{Thres}/(e \times \text{Gain})}$$

If we assume the gain will not change much, and the LED intensity will be the same if the same voltage is applied, we can define the relative efficiency by:

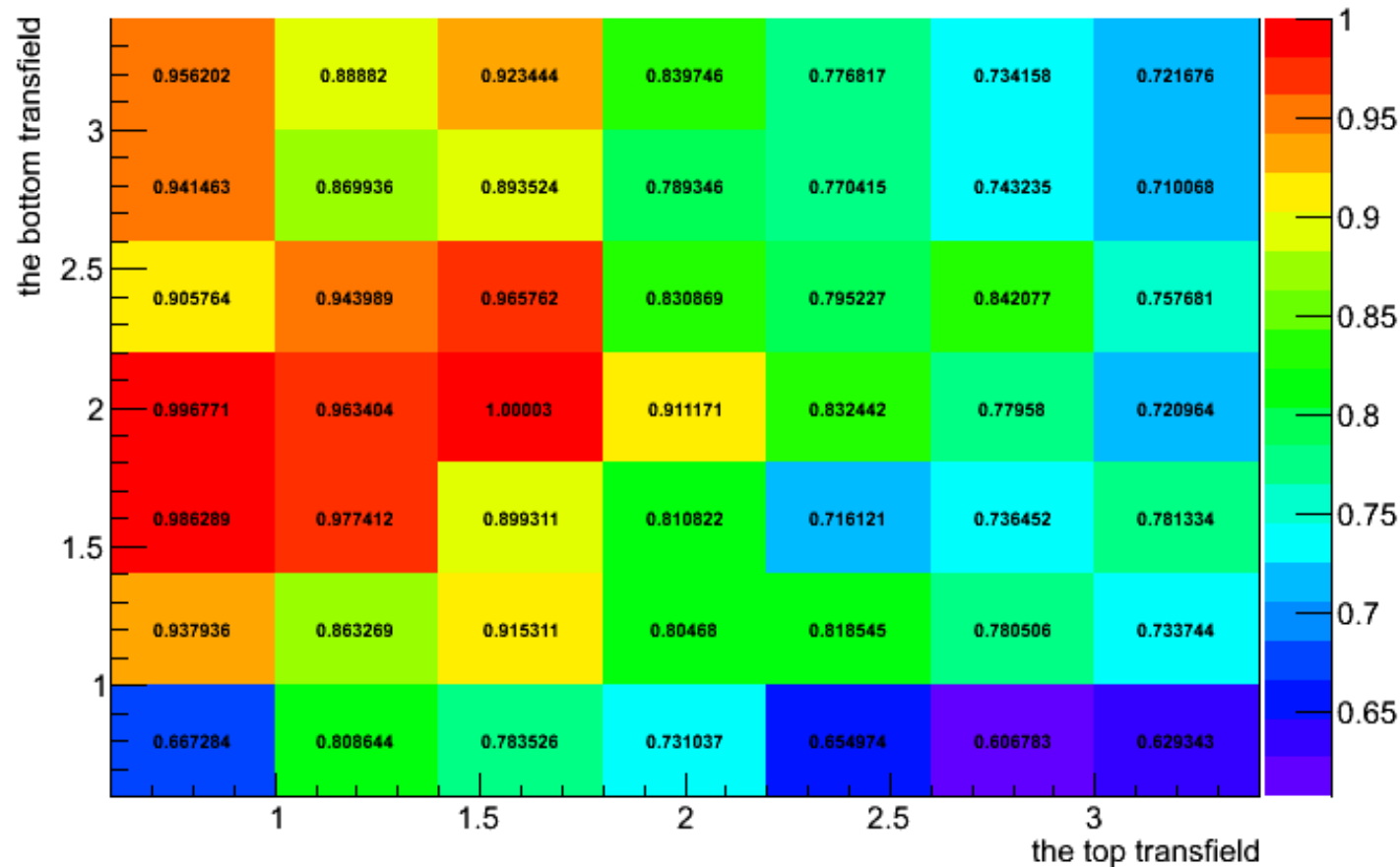
$$\epsilon_i = \frac{R_i}{R_0}$$

$$R_i = \text{Rate}_i / e^{-\text{Thres}/(e \times \text{Gain}_i)}$$

The “R” here can be get from gain MCA files, or by solving the function above.

Efficiency of aligned 2D distribution

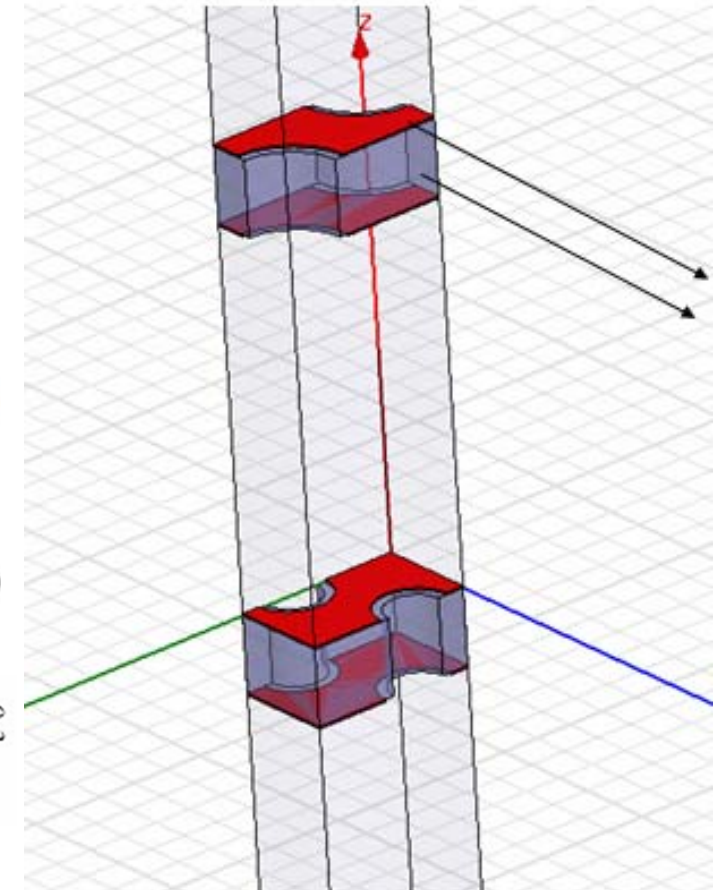
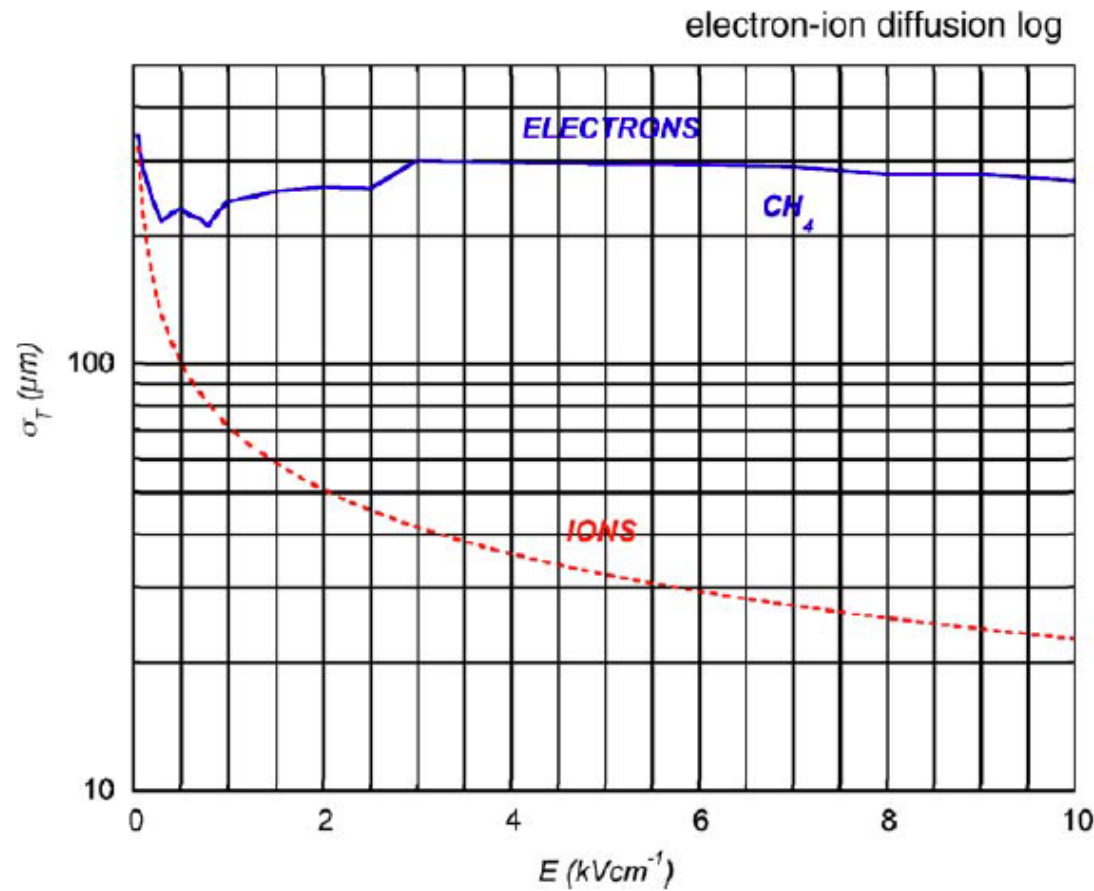
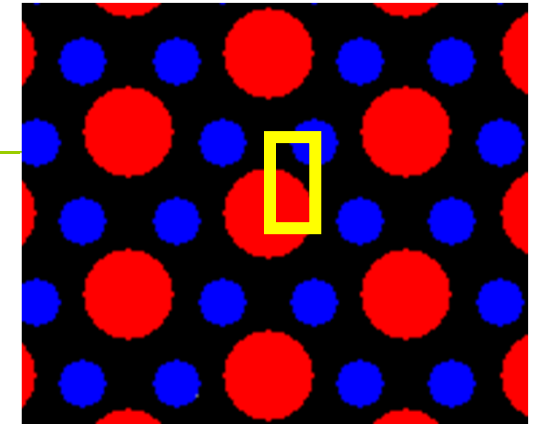
rate 2D map for transfer field scan for aligned TTHGEM



The result gives a same behavior as not-aligned configuration.

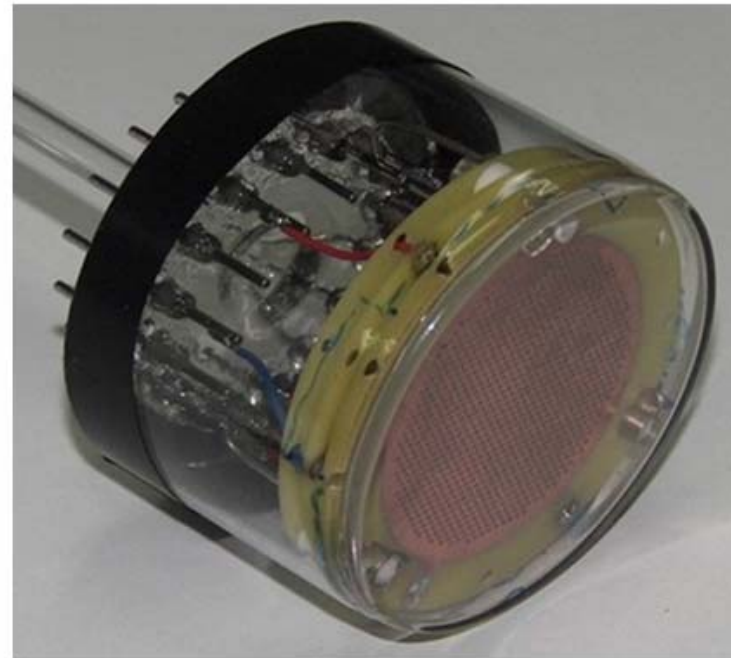
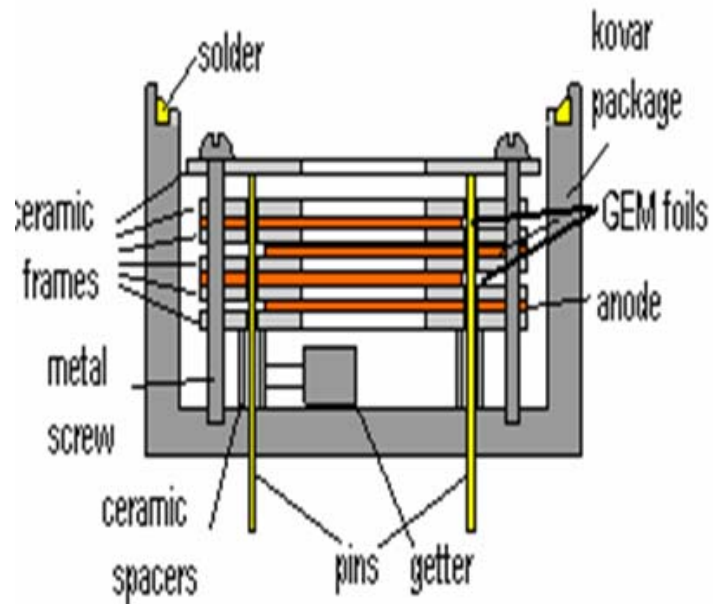
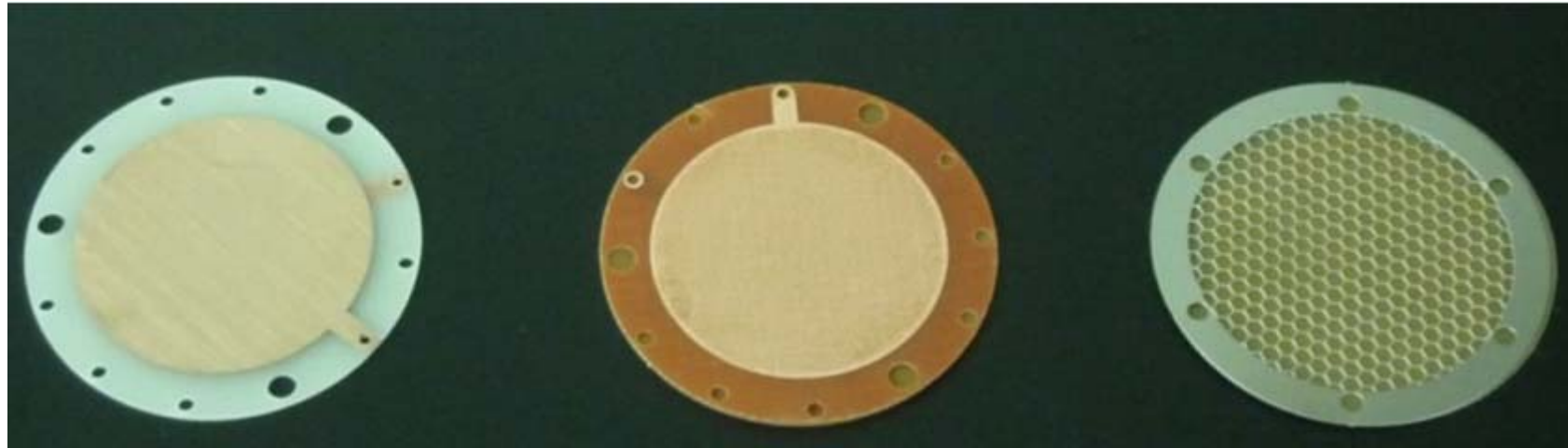
The result is got from MCA.

MC Simulation



Ions diffusion is much less than electrons
which proves this mis-aligned configuration is
effective to the IBF.

What've done in GUCAS



Conclusion

1. 93% of the IBF can be reduced by not-aligned configuration while the gain only decreased 17%.
2. The ions will mainly collected (60%~70%) by the layer where those ions are generated. So working under the minimum gain of the first layer THGEM is also important.

谢谢~

